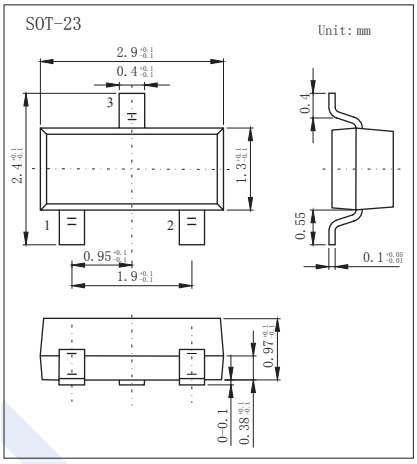
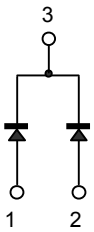
Switching Diodes

DAN202K (KAN202K)



■ Features

- Ultra high speed switching
- High reliability



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_{RM}	80	V
Reverse Voltage (DC)	V_R	80	
Average rectified forward current (Single)	Io	100	mA
Average rectified forward current (double)		150	
Forward Current (Single)	I_{FM}	300	
Forward Current (Double)		450	
Surge current (t=1us) (Single)	I_{surge}	4	A
Surge current (t=1us) (Double)		6	
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	I_R= 100 uA	80			V
Forward voltage	V_F	I_F= 100 mA			1.2	
Reverse voltage leakage current	I_R	V_R= 70 V			0.1	uA
Capacitance between terminals	C_t	V_R= 6 V, f= 1 MHz			3.5	pF
Reverse recovery time	t_{rr}	V_R=6V,I_F=5mA, R_L=50Ω			4	ns

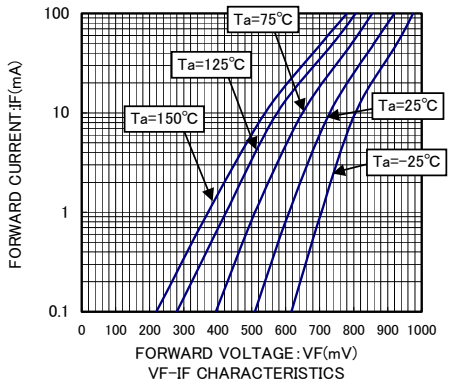
■ Marking

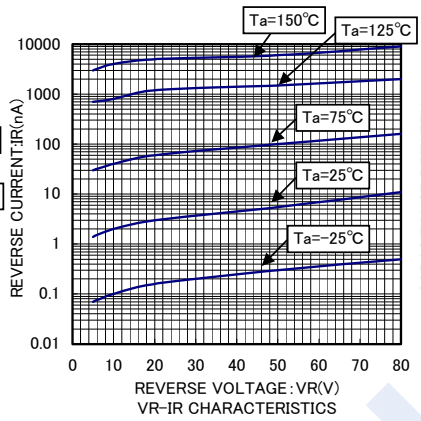
Marking	N*

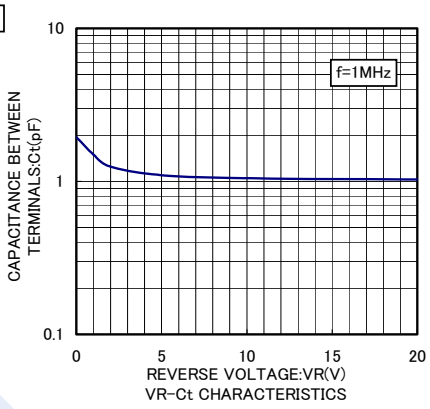
Switching Diodes

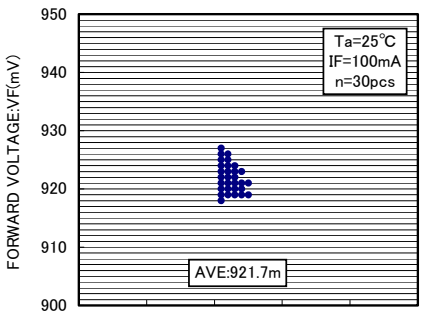
DAN202K (KAN202K)

■ Typical Characterisitics

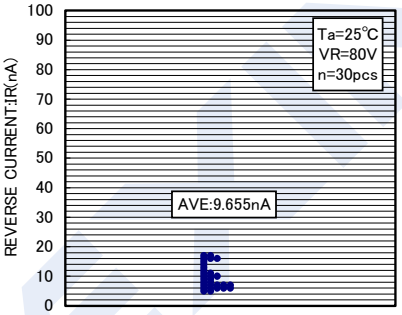




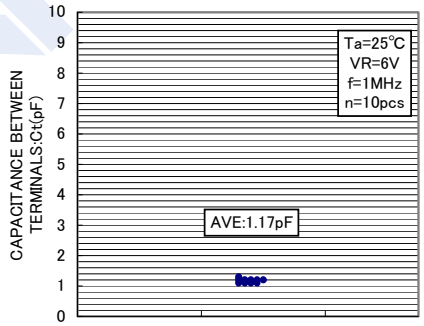




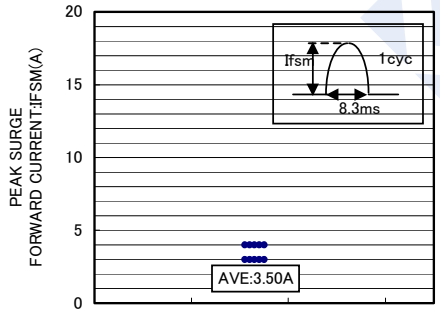
VF DISPERSION MAP



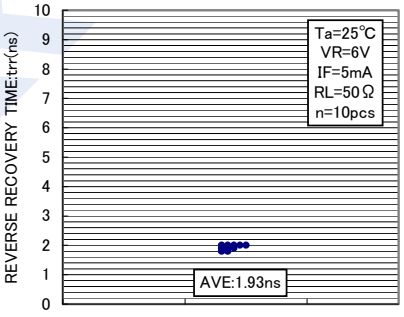
IR DISPERSION MAP



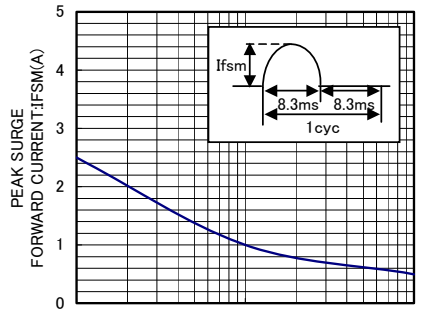
Ct DISPERSION MAP

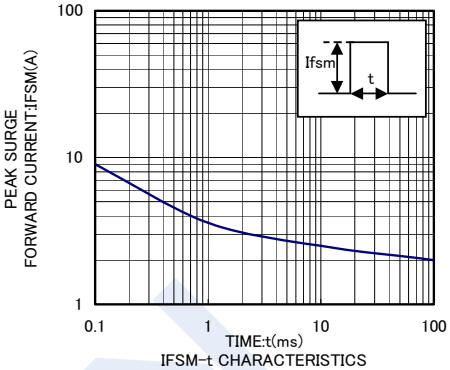


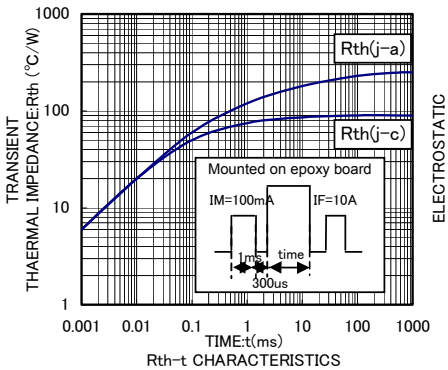
IFSM DISPERSION MAP

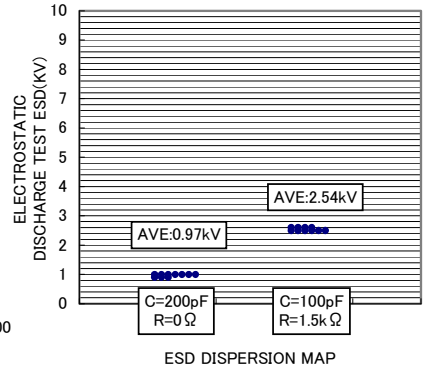


trr DISPERSION MAP









ESD DISPERSION MAP